

### AMENDMENTS TO THE SPECIFICATION

On page 2, please amend the paragraph beginning at line 7 as follows:

In general, a silicon oxide film ( $\text{SiO}_2$  film) is inferior in wettability with a layer of molten silicon due to a ~~small~~ large contact angle with respect to molten silicon. Therefore, the layer of molten silicon inconveniently agglomerates into a bulk in crystallization. When a crystal growth method of moving the interface between a molten region and a crystal region of a silicon layer by scanning with a laser beam is employed, the molten region is also moved following movement of a heated region, leading a remarkable tendency toward agglomerating. According to the non-patent literature 1, the silicon layer formed on the silicon oxide film is previously patterned in the form of a ribbon thereby reducing the area of the molten silicon layer.